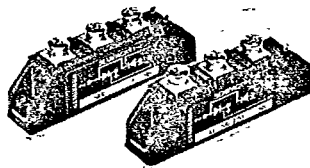


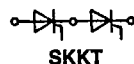
T-25-17

SEMIKRON

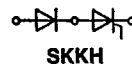
V _{RSM}	V _{RRM} V _{DRM}	(dv/dt) _{cr}	I _{TRMS} (maximum values for continuous operation)			
			75 A	95 A	75 A	95 A
			I _{TAV} (sin. 180; T _{case} = 74 °C)			
V	V	V/μs	48 A	60 A	48 A	60 A
500	400	500	SKKT 41/04 D	SKKT 56/04 D	SKKH 41/04 D	SKKH 56/04 D
700	600	500	SKKT 41/06 D	SKKT 56/06 D	SKKH 41/06 D	SKKH 56/06 D
900	800	500	SKKT 41/08 D	SKKT 56/08 D	SKKH 41/08 D	SKKH 56/08 D
1300	1200	500	SKKT 41/12 D	SKKT 56/12 D	SKKH 41/12 D	SKKH 56/12 D
		1000	SKKT 41/12 E	SKKT 56/12 E	-	-
1500	1400	1000	SKKT 41/14 E	SKKT 56/14 E	SKKH 41/14 E	SKKH 56/14 E
1700	1600	1000	SKKT 41/16 E	SKKT 56/16 E	SKKH 41/16 E	SKKH 56/16 E
1900	1800	1000	-	SKKT 56/18 E	-	SKKH 56/18 E
2100	2000	1000	-	SKKT 56/20 E	-	SKKH 56/20 E

SEMIPACK® 1**Thyristor/ Diode Modules****SKKT 41**
SKKT 56**SKKH 41**
SKKH 56

Symbol	Conditions	SKKT 41 SKKH 41	SKKT 56 SKKH 56
I _{TAV}	sin. 180; (T _{case} = ...)	48 A (74 °C) 40 A (85 °C)	60 A (74 °C) 55 A (80 °C)
I _D	B2/B6 T _{amb} = 35 °C; P 3/180 F	85 A/110 A	100 A/130 A
I _{RMS}	W1/W3 T _{amb} = 35 °C; P 3/180 F	105 A/3x85 A	130 A/3x100 A
I _{TSM}	T _{vj} = 25 °C	1000 A	1500 A
i ² t	T _{vj} = 125 °C	850 A	1250 A
	T _{vj} = 25 °C	5000 A ² s	11000 A ² s
	T _{vj} = 125 °C	3600 A ² s	8000 A ² s
t _{gd}	T _{vj} = 25 °C; I _G = 1 A; di _G /dt = 1 A/μs	1 μs	
t _{gr}	V _D = 0,67 · V _{DRM}	2 μs	
(di/dt) _{cr}	T _{vj} = 125 °C	typ. 100 A/μs	
t _q	T _{vj} = 125 °C	typ. 80 μs	
I _H	T _{vj} = 25 °C	typ. 150 mA; max. 250 mA	
I _L	T _{vj} = 25 °C; R _G = 33 Ω	typ. 300 mA; max. 600 mA	
V _T	T _{vj} = 25 °C; I _T = 200 A	max. 1,95 V	max. 1,65 V
V _{T(TO)}	T _{vj} = 125 °C	1 V	0,9 V
r _T	T _{vj} = 125 °C	4,5 mΩ	3,5 mΩ
I _{DD} ; I _{RD}	T _{vj} = 125 °C; V _{DD} = V _{DRM} ; V _{RD} = V _{RRM}	max. 15 mA	max. 15 mA
V _{GT}	T _{vj} = 25 °C; d. c.	3 V	
I _{GT}	T _{vj} = 25 °C; d. c.	150 mA	
V _{GD}	T _{vj} = 125 °C; d. c.	0,25 V	
I _{GD}	T _{vj} = 125 °C; d. c.	6 mA	
R _{thjc}	cont. sin. 180 } per thyristor/per module rec. 120 } (°C/W)	0,65/0,33 0,69/0,35 0,73/0,37	0,57/0,29 0,60/0,30 0,64/0,32
R _{thch}	0,2/0,1 °C/W		
T _{vj}	-40 ... +125 °C		
T _{stg}	-40 ... +125 °C		
V _{isol}	a. c. 50 Hz; r.m.s.; 1 s/1 min	3000 V ~ /2500 V ~	
M ₁	Case to heatsink	5 Nm/44 lb. in. ± 15 % ¹⁾	
M ₂	Busbars to terminals	3 Nm/26 lb. in. ± 15 %	
a		5 · 9,81 m/s ²	
w	approx.	120 g	
Case	→ page B 1-85	A 5 (SKKT 41) A 6 (SKKH 41)	A 5 (SKKT 56) A 6 (SKKH 56)



SKKT



SKKH

Features

- Heat transfer through ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

Typical Applications

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

¹⁾ See the assembly instructions

T-25-17

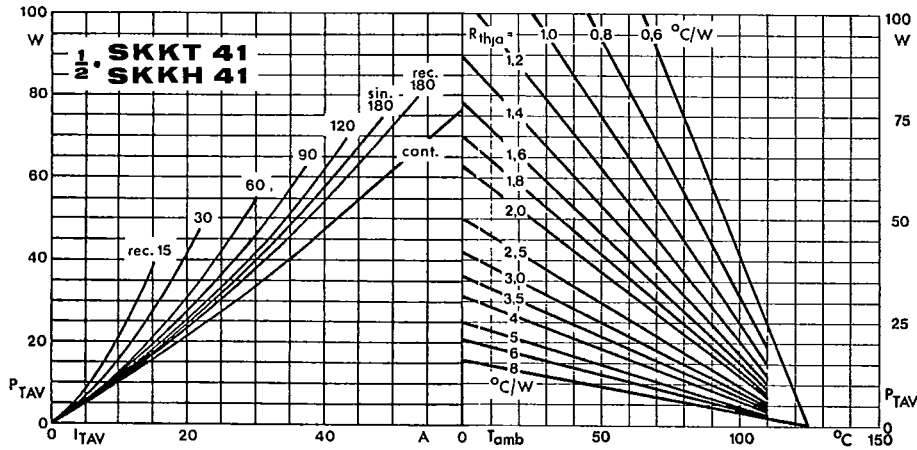


Fig. 1 a Power dissipation per thyristor vs. on-state current and ambient temperature

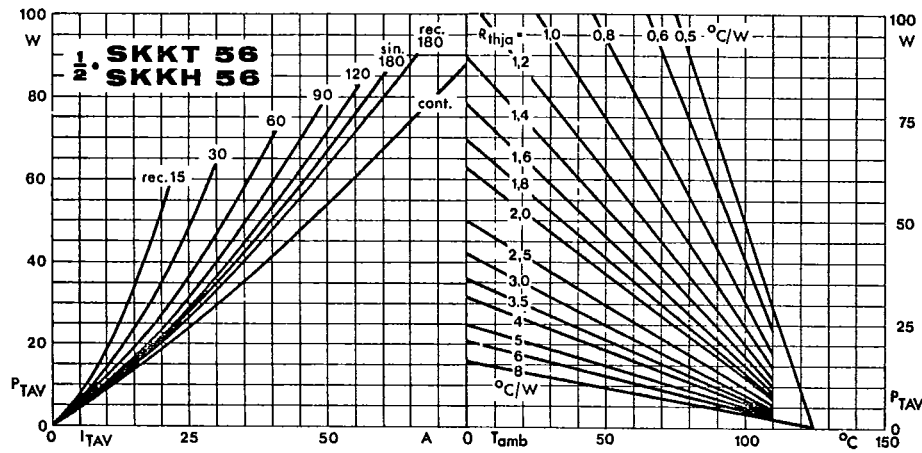


Fig. 1 b Power dissipation per thyristor vs. on-state current and ambient temperature

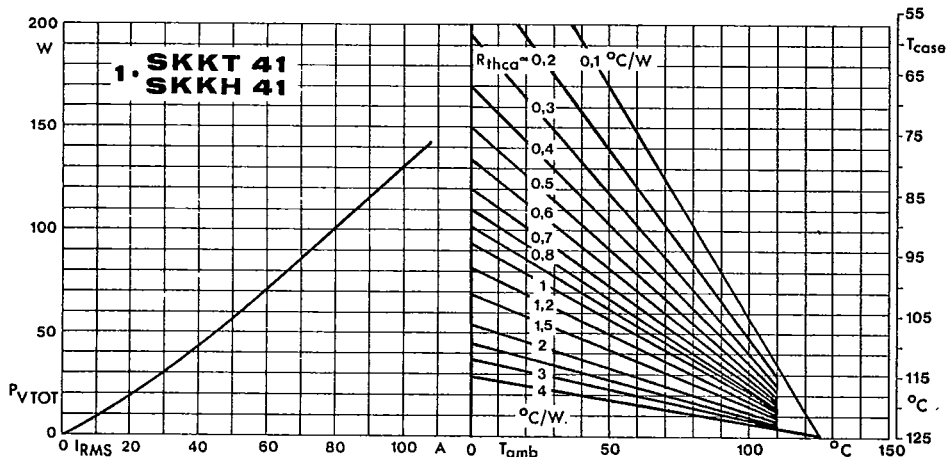


Fig. 2 a Power dissipation per module vs. rms current and case temperature

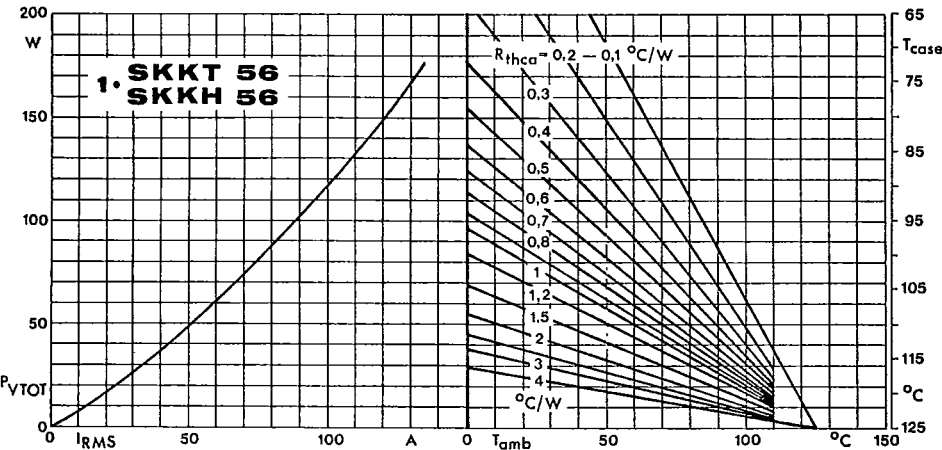


Fig. 2 b Power dissipation per module vs. rms current and case temperature

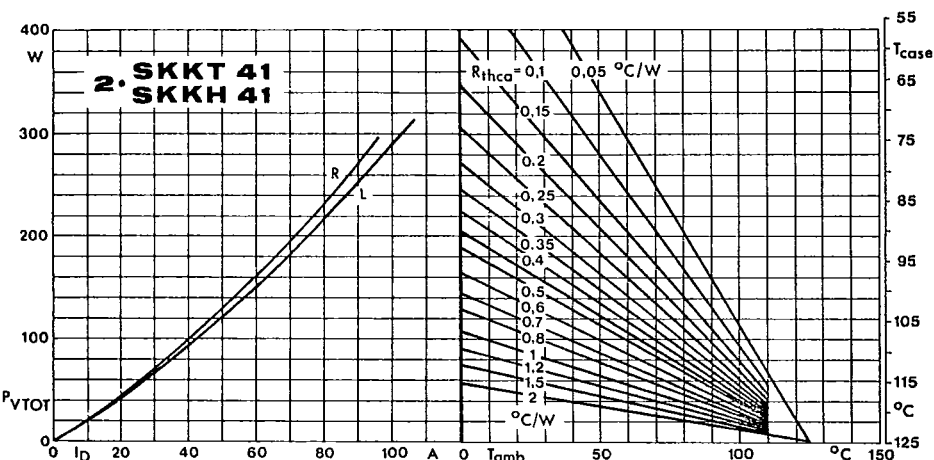


Fig. 3 a Power dissipation of two modules vs. direct current and case temperature

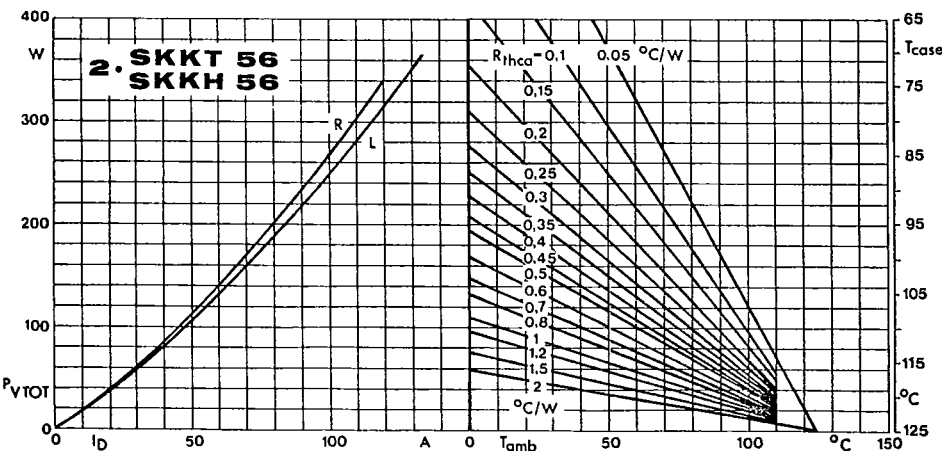


Fig. 3 b Power dissipation of two modules vs. direct current and case temperature

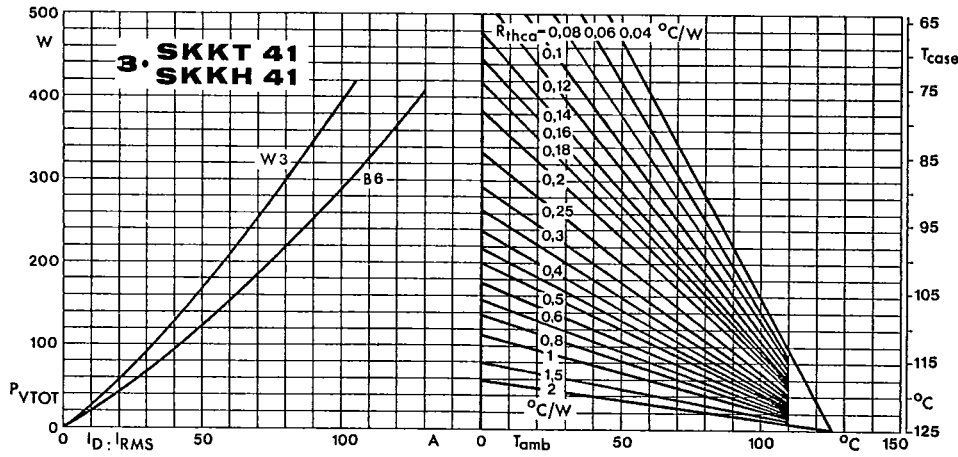


Fig. 4 a Power dissipation of three modules vs. direct and rms current and case temperature

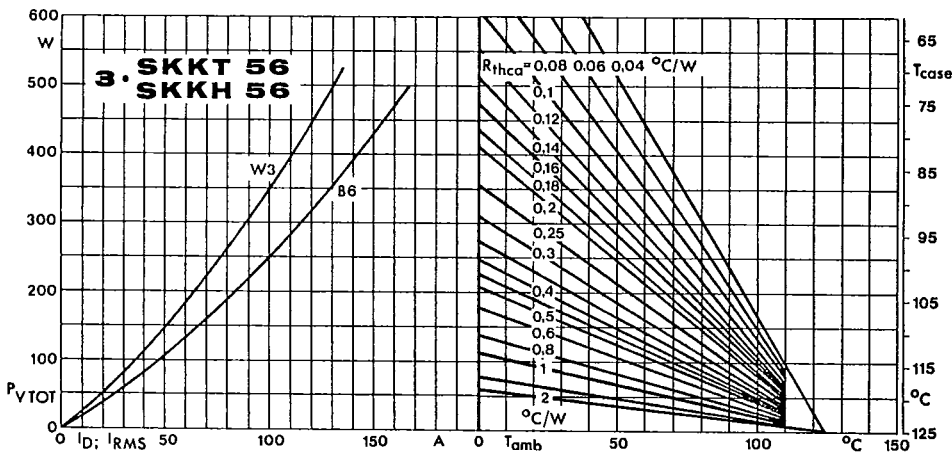


Fig. 4 b Power dissipation of three modules vs. direct and rms current and case temperature

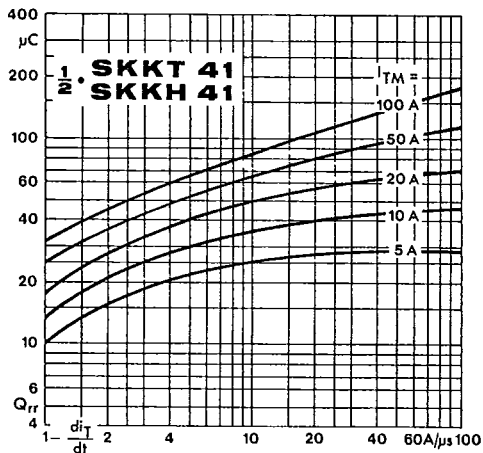


Fig. 5 a Recovered charge vs. current decrease

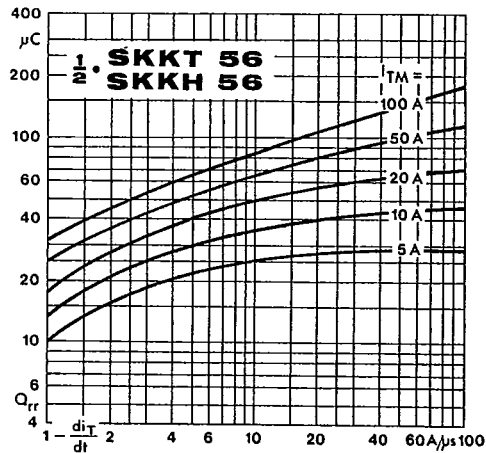


Fig. 5 b Recovered charge vs. current decrease

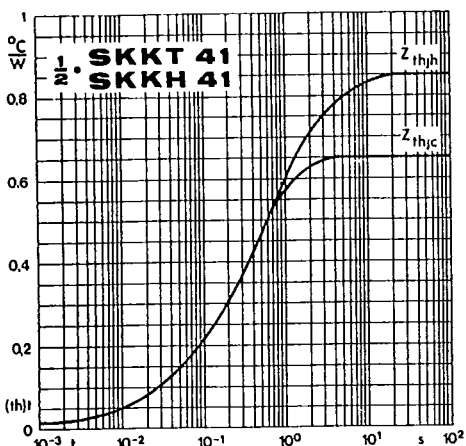


Fig. 6 a Transient thermal impedance vs. time

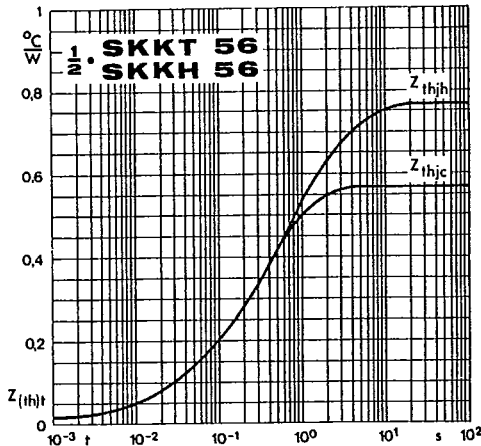


Fig. 6 b Transient thermal impedance vs. time

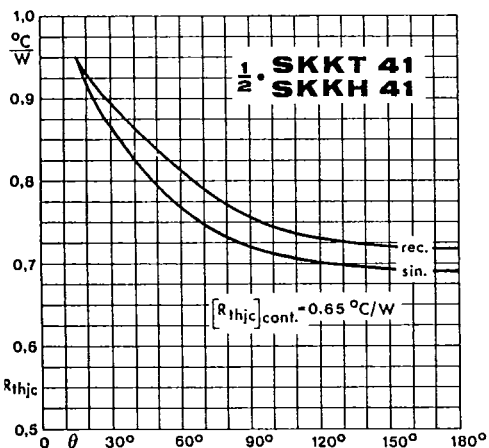


Fig. 7 a Thermal resistance vs. conduction angle

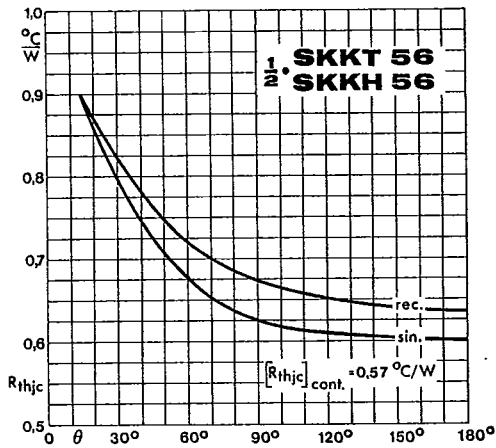


Fig. 7 b Thermal resistance vs. conduction angle

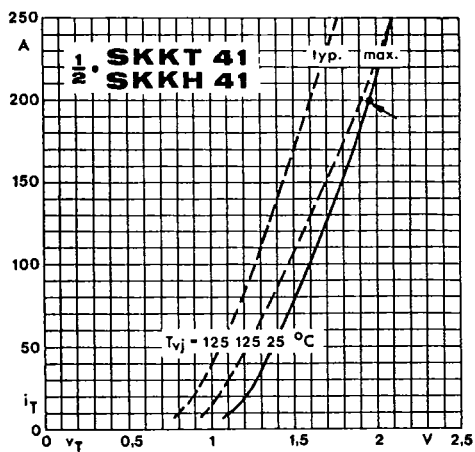


Fig. 8 a On-state characteristics

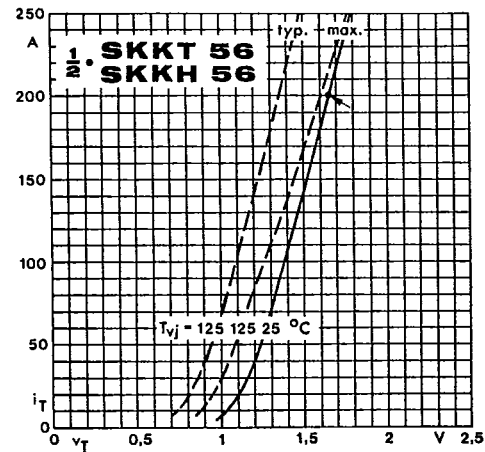


Fig. 8 b On-state characteristics

T-25-17

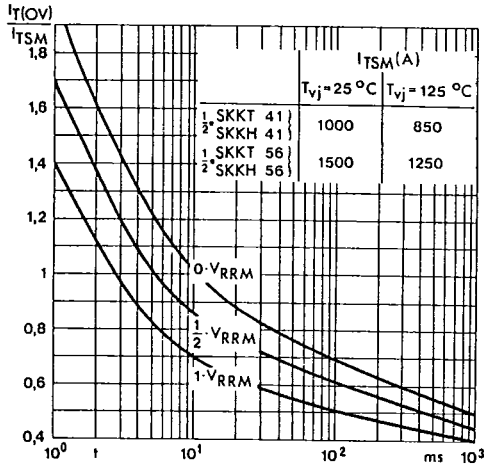


Fig. 9 Surge overload current vs. time

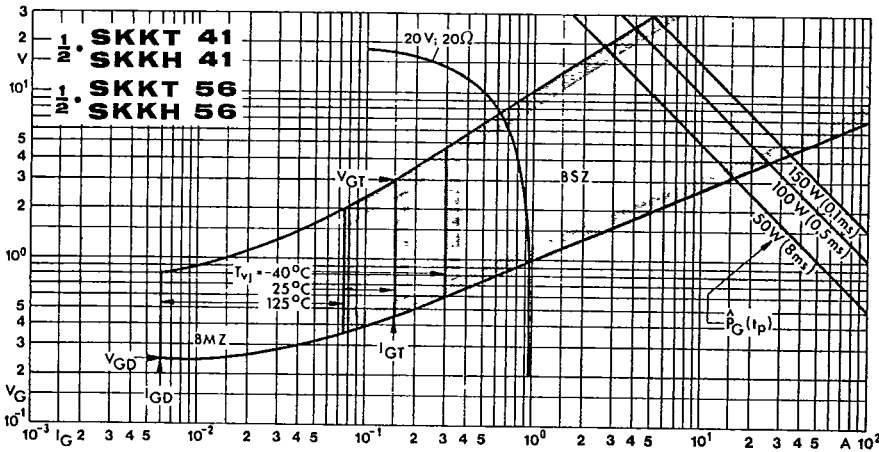


Fig. 10 Gate trigger characteristics